TOSHIBA **1SS402**

TENTATIVE

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1 S S 4 0 2

HIGH SPEED SWITCHING APPLICATIONS

Two independent diodes are mounted on four-pin ultra-small packages that are suitable for higher mounting densities.

 $: V_{F(3)} = 0.50 V \text{ (Typ.)}$ Low Forward Voltage

: $I_R = 0.5 \,\mu\text{A}$ (Max.) Low Reverse Current

Small Total Capacitance $: C_T = 3.9 pF (Typ.)$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Maximum (Peak) Reverse Voltage	$V_{ m RM}$	25	V	
Reverse Voltage	$V_{\mathbf{R}}$	20	V	
Maximum (Peak) Forward Current	$I_{\mathbf{FM}}$	100 (*)	mA	
Average Forward Current	IO	50 (*)	mA	
Surge Current (10ms)	I_{FSM}	1 (*)	A	
Power Dissipation	P	100	mW	
Junction Temperature	T_{j}	125	$^{\circ}\mathrm{C}$	
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	$^{\circ}\mathrm{C}$	

Unit in mm 1.25 ± 0.1 ANODE1 ANODE2 CATHODE2 USQ CATHODE1 **JEDEC EIAJ** TOSHIBA 1-2U1A

(*) Unit Rating. Total Rating = Unit Rating × 1.5

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	$I_{\mathrm{F}} = 1 \mathrm{mA}$	_	0.33	-	
	$V_{F(2)}$	$I_{\mathbf{F}} = 5 \text{ mA}$	_	0.38	-	V
	V _{F (3)}	$I_{ m F}=50{ m mA}$	_	0.50	0.55	
Reverse Current	I _{R (1)}	$V_R = 20 V$	_		0.5	μ A
Total Capacitance	C_{T}	$ m V_R = 0, \ f = 1 \ MHz$	_	3.9	5.0	pF

PIN ASSIGNMENT (TOP VIEW)







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